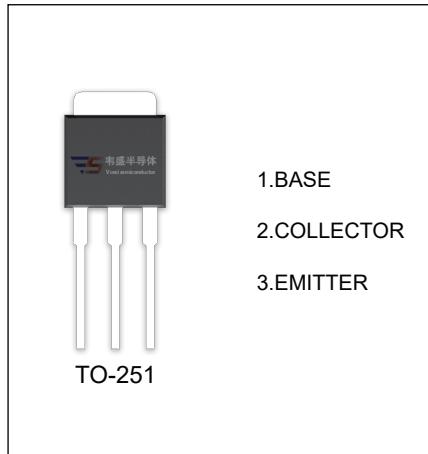


MJD2955 TRANSISTOR (PNP)

FEATURES

- for Applications General Amplifiers and Low Speed Switching Designed
- Electrically Similar to MJD3055
- DC Current Gain Specified to 10 Amperes



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_c	Collector Current -Continuous	-10	A
P_c	Collector Power Dissipation	1.25	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-200\text{ mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-70\text{V}, I_E=0$			-0.02	mA
	I_{CEO}	$V_{CB}=-30\text{V}, I_B=0$			-50	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.5	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=-4\text{V}, I_C=-4\text{A}$	20		100	
	$h_{FE(2)}$	$V_{CE}=-4\text{V}, I_C=-10\text{A}$	5			
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C=-4\text{A}, I_B=-0.4\text{A}$			-1.1	V
	$V_{CE(sat)(2)}$	$I_C=-10\text{A}, I_B=-3.3\text{A}$			-8	V
Base-emitter voltage	V_{BE}	$V_{CE}=-4\text{V}, I_C=-4\text{A}$			-1.8	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-0.5\text{A}, f=500\text{kHz}$	2			MHz